

**In the Claims:**

Please amend claims 4-5, 7 and 18, and add new claims 21-22 as indicated below.  
This listing of claims replaces all prior versions.

Claims 1-3 (Cancelled)

4. (Currently amended) A method of manufacturing a semiconductor device comprising the step of depositing an epitaxial layer based on Group IV elements on a silicon substrate by Chemical Vapor Deposition using source gases, and including employing nitrogen as a carrier gas,

wherein the epitaxial layer comprises a SiGe epitaxial layer, and

wherein the method is carried out at a temperature between 500°C and 600°C.

5. (Currently amended) A method of manufacturing a semiconductor device comprising the step of depositing an epitaxial layer based on Group IV elements on a silicon substrate by Chemical Vapor Deposition using source gases, and including employing nitrogen as a carrier gas,

~~The method as claimed in claim 4, wherein the epitaxial layer further comprises  $Si_{1-x-y}Ge_xC_y$ .~~

6. (Cancelled)

7. (Currently amended) The method as claimed in claim 5 [[4]], which is carried out at a temperature that facilitates a CVD growth rate of an epitaxial layer that is substantially greater than a CVD growth rate of such an epitaxial layer using hydrogen as a carrier gas.

Claims 8-17 (Cancelled)

18. (Currently amended) A method as claimed in claim 4, wherein the source gases include  $SiH_4$  and  $GeH_4$  which is carried out at a temperature of less than about 600°C.

19. (Previously presented) A method as claimed in claim 5, which is carried out at a temperature of less than about 600°C.

20. (Cancelled)

21. (New) A method as claimed in claim 5, which is carried out at a temperature between 500°C and 600°C.

22. (New) A method as claimed in claim 5, wherein the source gases include SiH<sub>4</sub>, GeH<sub>4</sub> and SiH<sub>3</sub>CH<sub>3</sub>.